

OSRAM GF PUSRA1.25

Datasheet

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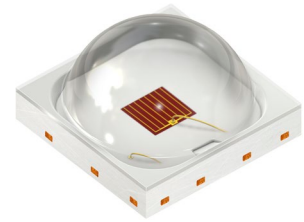


OSCONIQ™ P 3737 (2W)

GF PUSRA1.25

High-power LED with our ams OSRAM's latest chip technology, delivering industry leading performance, superior robustness and long lifetime. With the introduction of a new color (Red 640 nm) the family offers five colors for ease of design and high flexibility for all your horticulture spectrum needs.

The OSCONIQ™ P 3737 family offers Hyper Red (660 nm), Red (640nm), Deep Blue (450 nm), Far Red (730 nm) and Horti White which can cater to both narrow spectrum and full spectrum solutions to meet all crop needs for both greenhouses and vertical farms.



Applications

- Agriculture & Horticulture
- Entertainment
- Indoor Lighting
- Outdoor & Industrial Lighting

Features

- Package: SMD epoxy package with silicone lens
- Typ. Radiation: 120°
- ESD: 8 kV acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 3B)
- Radiant Flux (@ 700mA): typ. 901 mW @ 25°C; typ. 834 mW @ 85°C
- Radiant Efficiency (@ 700mA): typ. 64.1% @ 25°C; typ. 61.1% @ 85°C
- Photon Flux (@ 700mA): typ. 5.44 $\mu\text{mol/s}$ @ 25°C; typ. 5.10 $\mu\text{mol/s}$ @ 85°C
- Photon Flux Efficacy (@ 700mA): typ. 3.87 $\mu\text{mol/J}$ @ 25°C; typ. 3.73 $\mu\text{mol/J}$ @ 85°C
- ThinFilm LED chip designed and manufactured in Germany

Ordering Information

Type	Photon Flux ¹⁾ $I_F = 700 \text{ mA}$ Φ_P	Ordering Code
GF PUSRA1.25-SHSK-1-1	4.60 ... 5.25 $\mu\text{mol/s}$	Q65113A8573
GF PUSRA1.25-SHSK-1-1F1J	4.60 ... 5.25 $\mu\text{mol/s}$	Q65113A7878
GF PUSRA1.25-SJSL-1-1C1F	4.80 ... 5.50 $\mu\text{mol/s}$	Q65115A1475

Maximum Ratings

Parameter	Symbol		Values
Operating Temperature	T_{op}	min.	-40 °C
		max.	125 °C
Storage Temperature	T_{stg}	min.	-40 °C
		max.	125 °C
Junction Temperature	T_j	max.	135 °C
Forward current	I_F	min.	100 mA
		max.	1400 mA
Surge Current $t \leq 10 \mu s$; $D = 0.005$; $T_j = 85 \text{ °C}$	I_{FS}	max.	2000 mA
Reverse voltage ²⁾	V_R	Not designed for reverse operation	
ESD withstand voltage acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 3B)	V_{ESD}	8 kV	

Characteristics

$I_F = 700 \text{ mA}$; $T_J = 85 \text{ °C}$

Parameter	Symbol		Values
Peak Wavelength	λ_{peak}	typ.	738 nm
Centroid Wavelength ³⁾ $I_F = 700 \text{ mA}$	$\lambda_{\text{centroid}}$	min. typ. max.	720 nm 731 nm 750 nm
Spectral Bandwidth at 50% $I_{\text{rel,max}}$	$\Delta\lambda$	typ.	35 nm
Viewing angle at 50% I_V	2ϕ	typ.	130 °
Forward Voltage ⁴⁾ $I_F = 700 \text{ mA}$	V_F	min. typ. max.	1.85 V 1.95 V 2.20 V
Reverse current ²⁾	I_R		Not designed for reverse operation
Electrical thermal resistance junction/solderpoint with efficiency $\eta_e = 61.1 \text{ %}$	$R_{\text{thJS elec.}}$	typ.	2.1 K / W

Brightness Groups

Group	Photon Flux ¹⁾ $I_F = 700 \text{ mA}$ min. Φ_P	Photon Flux ¹⁾ $I_F = 700 \text{ mA}$ max. Φ_P	PF/W typ.	Total Radiant Flux min. Φ_E	Total Radiant Flux max. Φ_E
SH	4.60 $\mu\text{mol/s}$	4.80 $\mu\text{mol/s}$	3.44 $\mu\text{mol/J}$	753 mW	786 mW
SJ	4.80 $\mu\text{mol/s}$	5.00 $\mu\text{mol/s}$	3.59 $\mu\text{mol/J}$	786 mW	818 mW
SK	5.00 $\mu\text{mol/s}$	5.25 $\mu\text{mol/s}$	3.75 $\mu\text{mol/J}$	818 mW	859 mW
SL	5.25 $\mu\text{mol/s}$	5.50 $\mu\text{mol/s}$	3.94 $\mu\text{mol/J}$	859 mW	900 mW

Note: [*] Photon Flux includes wavelengths between 280 and 800 nm.

Note: [**] Radiant Flux values are for reference only.

Forward Voltage Groups

Group	Forward Voltage ⁴⁾ $I_F = 700 \text{ mA}$ min. V_F	Forward Voltage ⁴⁾ $I_F = 700 \text{ mA}$ max. V_F
1C	1.85 V	1.90 V
1D	1.90 V	1.95 V
1E	1.95 V	2.00 V
1F	2.00 V	2.05 V
1G	2.05 V	2.10 V
1H	2.10 V	2.15 V
1J	2.15 V	2.20 V

Centroid Wavelength

Group	Centroid Wavelength ³⁾ $I_F = 700 \text{ mA}$ min. $\lambda_{\text{centroid}}$	Centroid Wavelength ³⁾ $I_F = 700 \text{ mA}$ max. $\lambda_{\text{centroid}}$
1	720 nm	750 nm

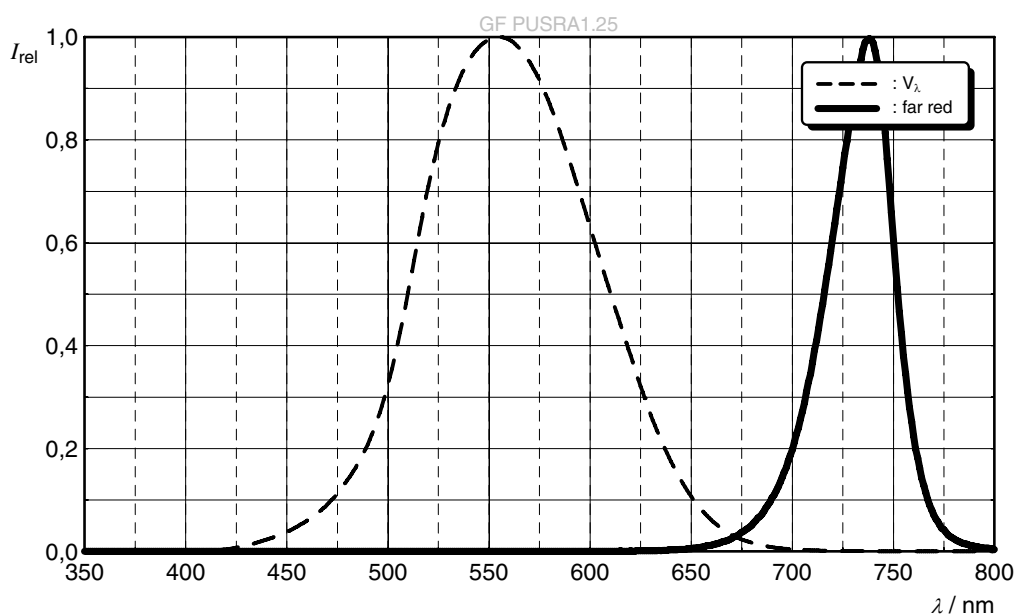
Group Name on Label

Example: SH-1-1C

Brightness	Wavelength	Forward Voltage
SH	1	1C

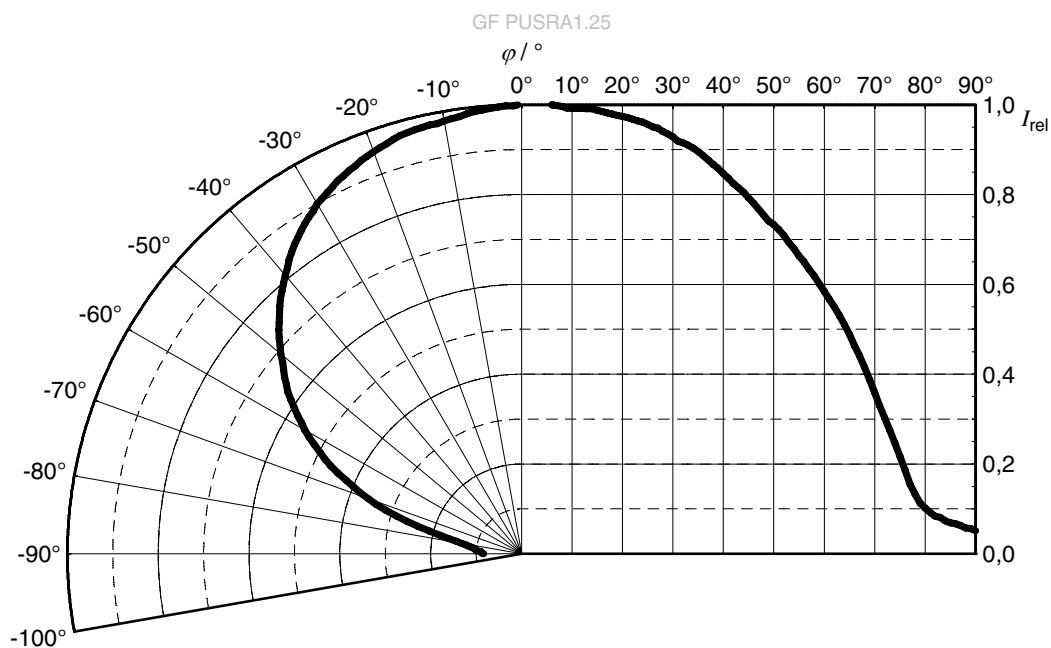
Relative Spectral Emission ⁵⁾

$I_{\text{rel}} = f(\lambda)$; $I_F = 700 \text{ mA}$; $T_J = 85^\circ\text{C}$



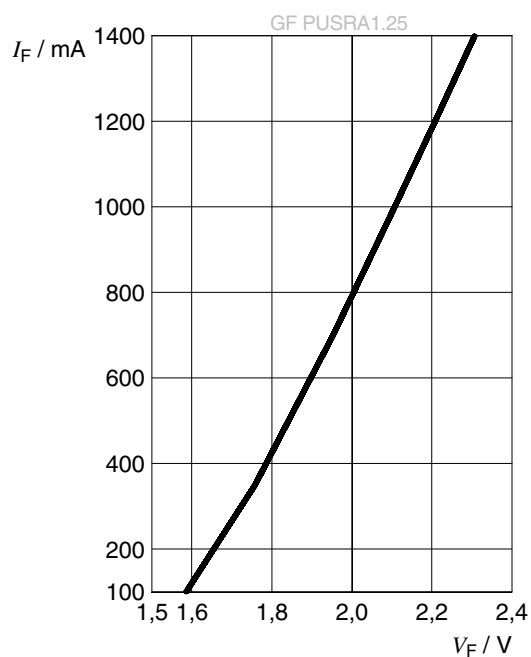
Radiation Characteristics ⁵⁾

$I_{\text{rel}} = f(\varphi)$; $T_J = 85^\circ\text{C}$



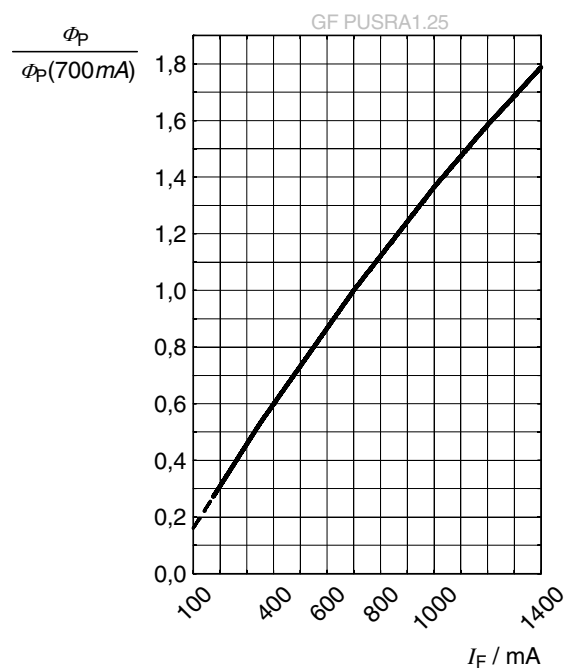
Forward current ⁵⁾

$$I_F = f(V_F); T_J = 85\text{ °C}$$



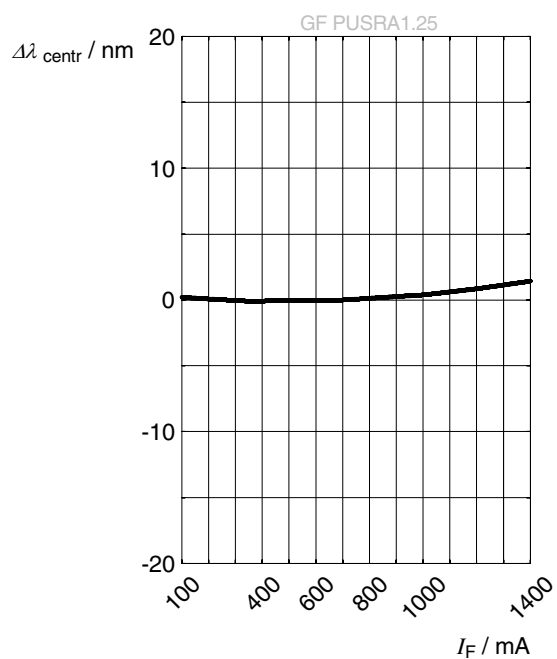
Relative Photon Flux ^{5), 6)}

$$\Phi_p / \Phi_p(700\text{ mA}) = f(I_F); T_J = 85\text{ °C}$$



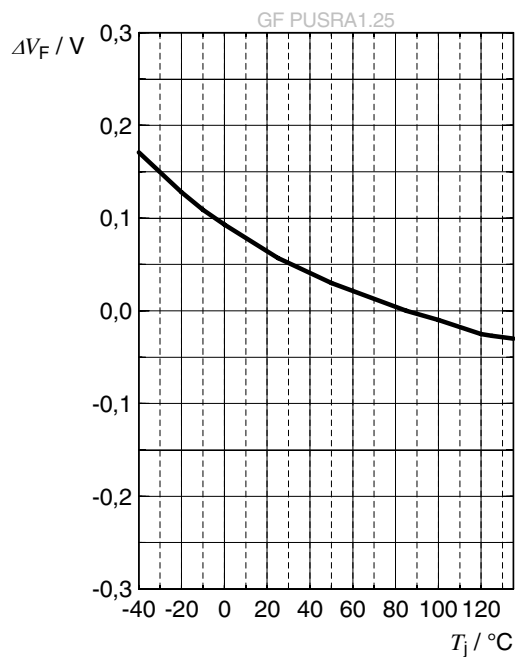
Centroid Wavelength ⁵⁾

$$\Delta\lambda_{\text{centr}} = f(I_F); T_J = 85\text{ °C}$$



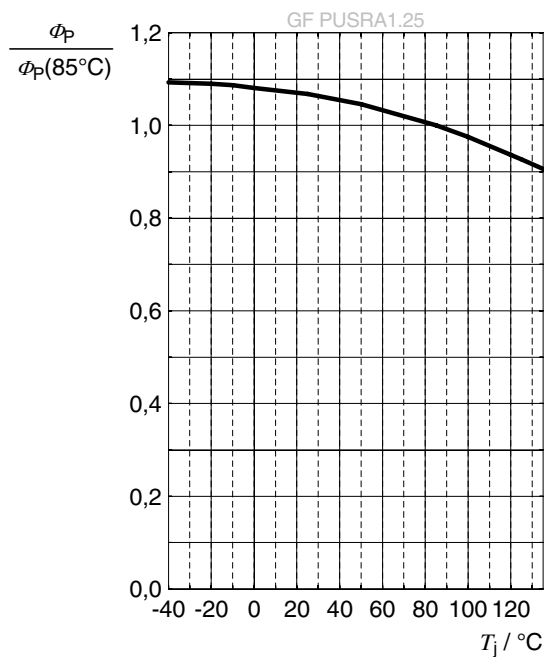
Forward Voltage ⁵⁾

$$\Delta V_F = V_F - V_F(85^\circ\text{C}) = f(T_j); I_F = 700\text{ mA}$$



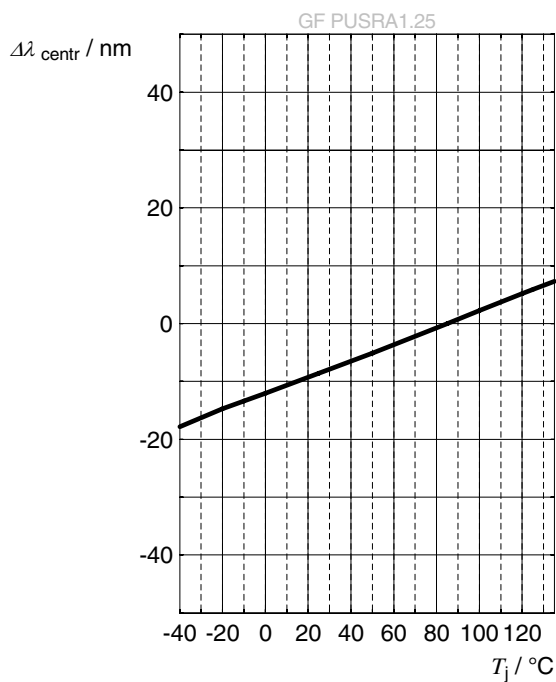
Relative Photon Flux ⁵⁾

$$\Phi_p / \Phi_p(85^\circ\text{C}) = f(T_j); I_F = 700\text{ mA}$$



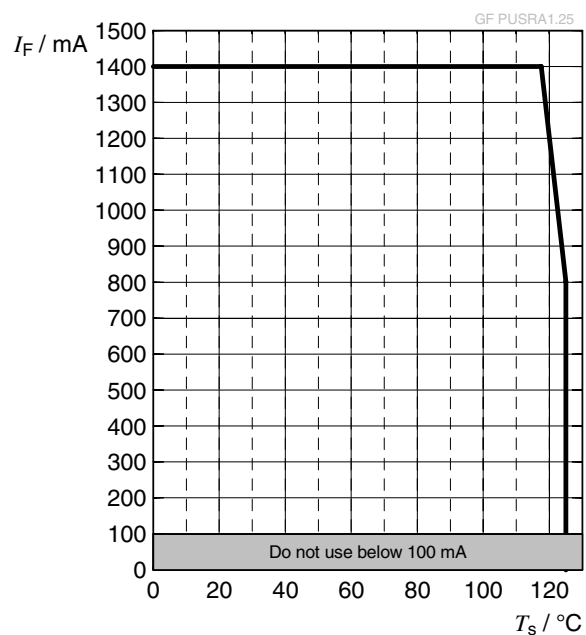
Centroid Wavelength ⁵⁾

$$\Delta \lambda_{\text{centr}} = \lambda_{\text{centr}} - \lambda_{\text{centr}}(85^\circ\text{C}) = f(T_j); I_F = 700\text{ mA}$$

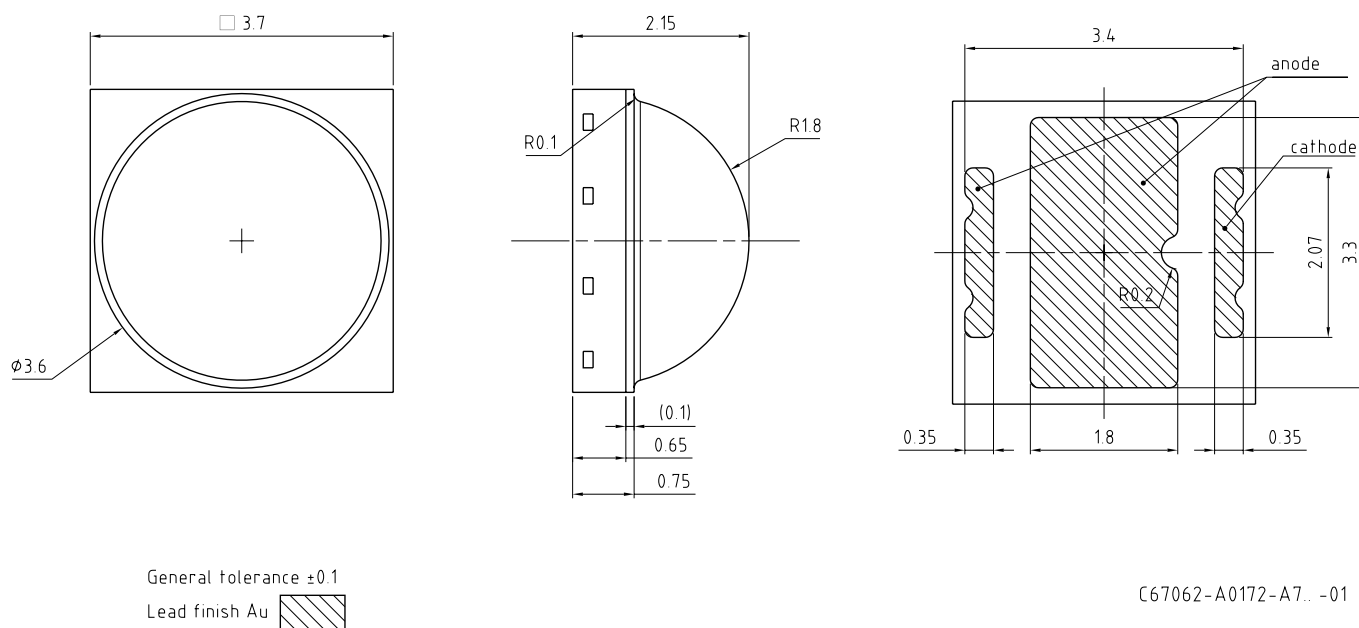


Max. Permissible Forward Current ⁷⁾

$$I_F = f(T)$$



Dimensional Drawing ⁸⁾



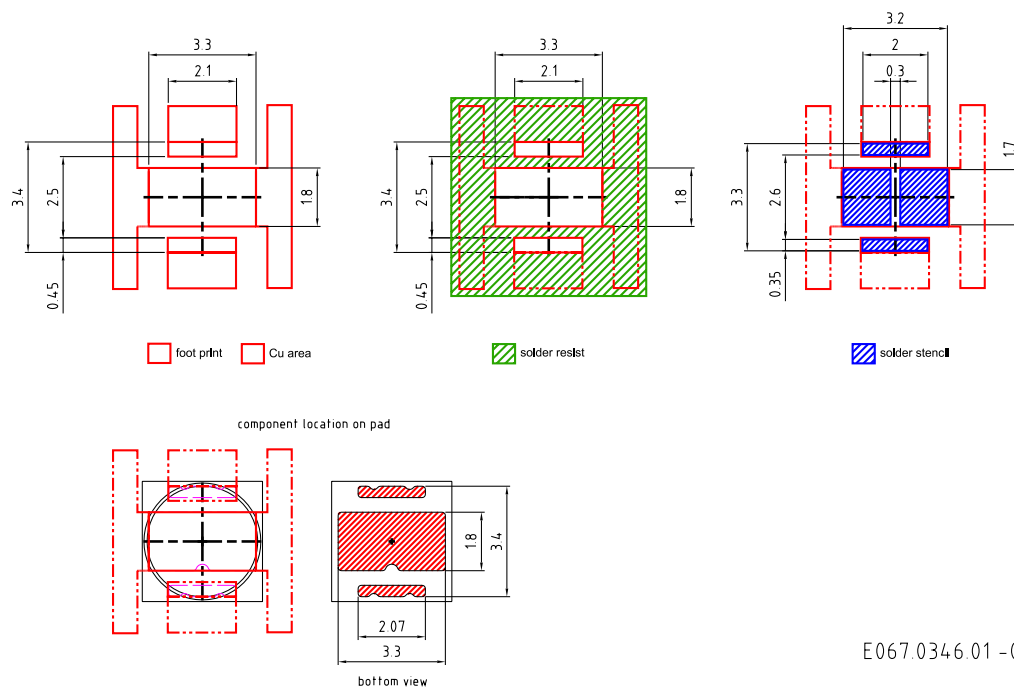
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Further Information:

Approximate Weight: 43.0 mg

ESD advice: The device is protected by ESD device which is connected in parallel to the Chip.

Recommended Solder Pad ⁸⁾

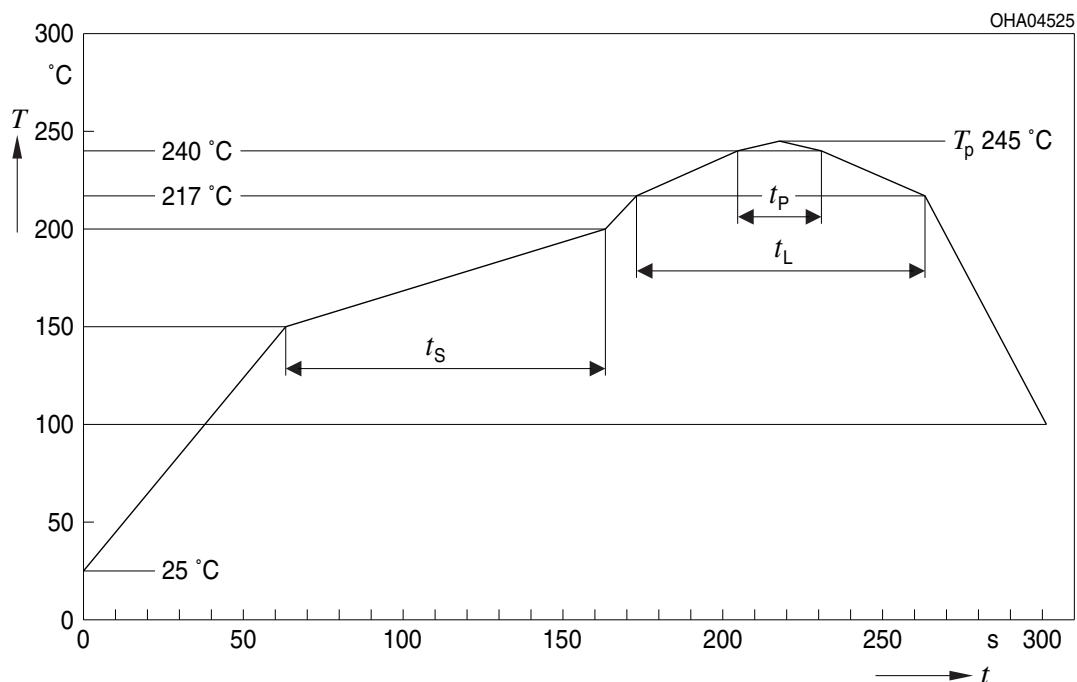


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For superior solder joint connectivity results we recommend soldering under standard nitrogen atmosphere. Package not suitable for ultra sonic cleaning.

Reflow Soldering Profile

Product complies to MSL Level 2 acc. to JEDEC J-STD-020E

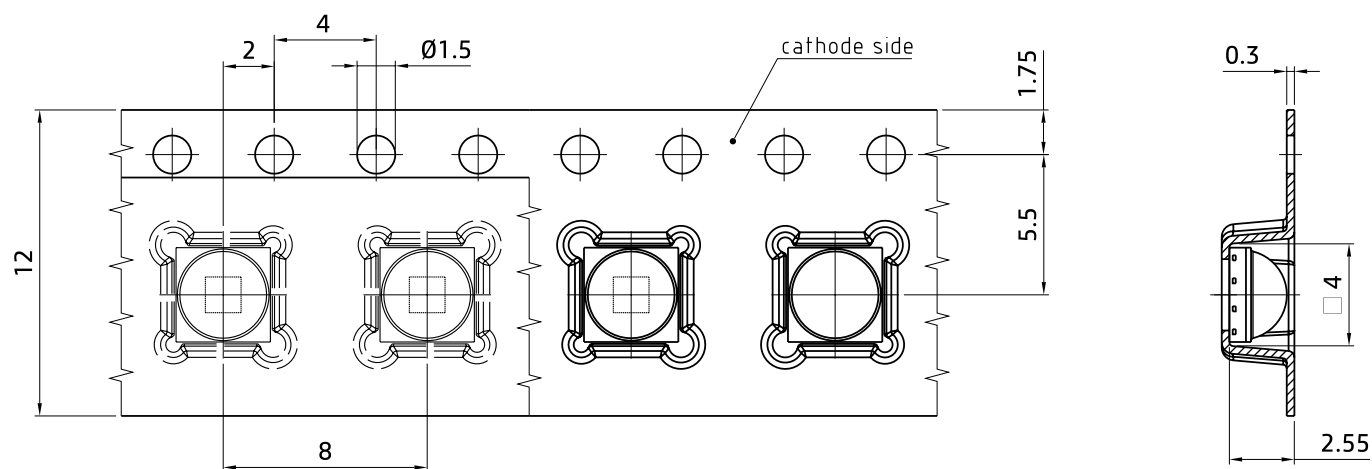


Profile Feature	Symbol	Pb-Free (SnAgCu) Assembly			Unit
		Minimum	Recommendation	Maximum	
Ramp-up rate to preheat ^{*)} 25 °C to 150 °C			2	3	K/s
Time t_s T_{Smin} to T_{Smax}	t_s	60	100	120	s
Ramp-up rate to peak ^{*)} T_{Smax} to T_p			2	3	K/s
Liquidus temperature	T_L		217		$^{\circ}\text{C}$
Time above liquidus temperature	t_L		80	100	s
Peak temperature	T_p		245	260	$^{\circ}\text{C}$
Time within 5 °C of the specified peak temperature $T_p - 5\text{ K}$	t_p	10	20	30	s
Ramp-down rate* T_p to 100 °C			3	6	K/s
Time 25 °C to T_p				480	s

All temperatures refer to the center of the package, measured on the top of the component

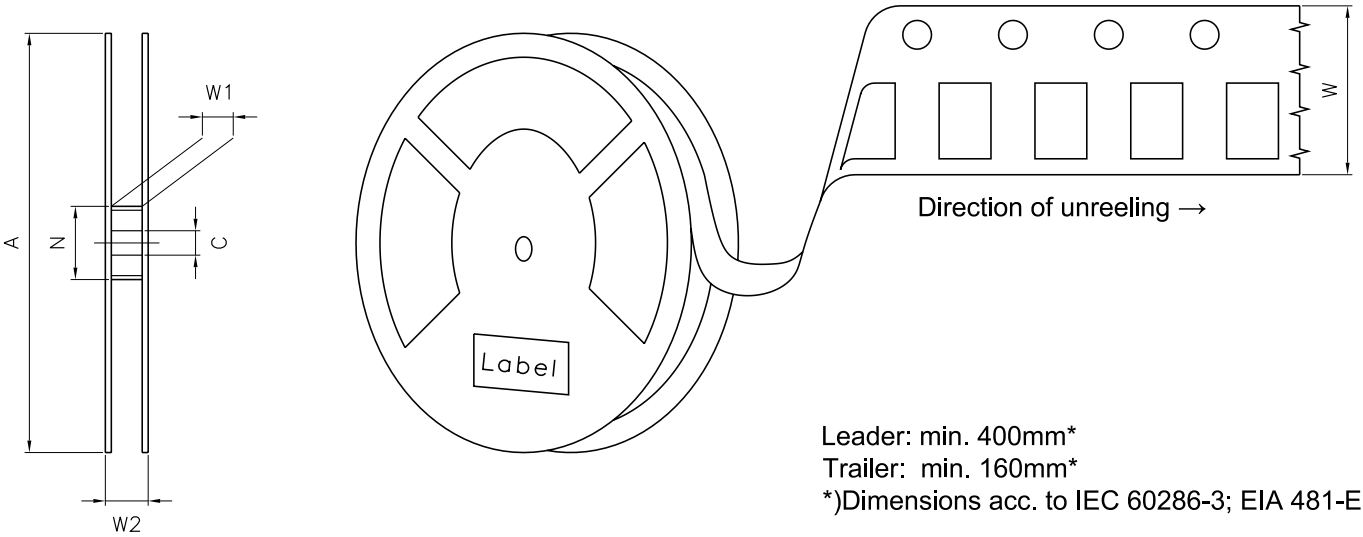
* slope calculation DT/Dt : Dt max. 5 s; fulfillment for the whole T-range

Taping ⁸⁾



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Tape and Reel ⁹⁾



Reel Dimensions

A	W	N _{min}	W ₁	W _{2 max}	Pieces per PU
330 mm	12 + 0.3 / - 0.1 mm	60 mm	12.4 + 2 mm	18.4 mm	3000

OSRAM		LX XXXX	BIN1: XX-XX-X-XXX-X
		RoHS Compliant	
(6P) BATCH NO: 1234567890			
			ML Temp ST X XXX °C X
(1T) LOT NO: 1234567890	(9D) D/C: 1234		
		Pack: RXX DEMY XXX X_X123_1234.1234 X	
(X) PROD NO: 123456789	(Q) QTY: 9999	(G) GROUP: XX-XX-X-X	

[illegible]

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Notes

The evaluation of eye safety occurs according to the standard IEC 62471:2006 (photo biological safety of lamps and lamp systems). Within the risk grouping system of this IEC standard, the device specified in this data sheet fall into the class **low risk (exposure time 100 s)**. Under real circumstances (for exposure time, conditions of the eye pupils, observation distance), it is assumed that no endangerment to the eye exists from these devices. As a matter of principle, however, it should be mentioned that intense light sources have a high secondary exposure potential due to their blinding effect. When looking at bright light sources (e.g. headlights), temporary reduction in visual acuity and afterimages can occur, leading to irritation, annoyance, visual impairment, and even accidents, depending on the situation.

Subcomponents of this device contain, in addition to other substances, metal filled materials including silver. Metal filled materials can be affected by environments that contain traces of aggressive substances. Therefore, we recommend that customers minimize device exposure to aggressive substances during storage, production, and use. Devices that showed visible discoloration when tested using the described tests above did show no performance deviations within failure limits during the stated test duration. Respective failure limits are described in the IEC60810.

This device is designed for specific/recommended applications only. Please consult OSRAM Opto Semiconductors Sales Staff in advance for detailed information on other non-recommended applications (e.g. automotive).

Change management for this component is aligned with the requirements of the lighting market.

For further application related information please visit <https://ams-osram.com/support/application-notes>

Disclaimer

Attention please!

The information describes the type of component and shall not be considered as assured characteristics. Terms of delivery and rights to change design reserved. Due to technical requirements components may contain dangerous substances.

For information on the types in question please contact our Sales Organization.

If printed or downloaded, please find the latest version on our website.

Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

Product and functional safety devices/applications or medical devices/applications

Our components are not developed, constructed or tested for the application as safety relevant component or for the application in medical devices.

Our products are not qualified at module and system level for such application.

In case buyer – or customer supplied by buyer – considers using our components in product safety devices/ applications or medical devices/applications, buyer and/or customer has to inform our local sales partner immediately and we and buyer and /or customer will analyze and coordinate the customer-specific request between us and buyer and/or customer.

Glossary

- 1) **Brightness:** Brightness values are measured during a current pulse of typically 10 ms, with a tolerance of +/- 7%.
- 2) **Reverse Operation:** Not designed for reverse operation. Continuous reverse operation can cause migration and damage of the device.
- 3) **Wavelength:** The wavelength is measured at a current pulse of typically 10 ms, with a tolerance of ± 0.5 nm.
- 4) **Forward Voltage:** The Forward voltage is measured during a current pulse duration of typically 1 ms with a tolerance of ± 0.05 V.
- 5) **Typical Values:** Due to the special conditions of the manufacturing processes of semiconductor devices, the typical data or calculated correlations of technical parameters can only reflect statistical figures. These do not necessarily correspond to the actual parameters of each single product, which could differ from the typical data and calculated correlations or the typical characteristic line. If requested, e.g. because of technical improvements, these typ. data will be changed without any further notice.
- 6) **Characteristic curve:** In the range where the line of the graph is broken, you must expect higher differences between single devices within one packing unit.
- 7) **Thermal Resistance:** $R_{th\ max}$ is based on statistic values (6σ) used for Derating.
- 8) **Tolerance of Measure:** Unless otherwise noted in drawing, tolerances are specified with ± 0.1 and dimensions are specified in mm.
- 9) **Tape and Reel:** All dimensions and tolerances are specified acc. IEC 60286-3 and specified in mm.

Revision History

Version	Date	Change
1.0	2024-04-08	Initial Version
1.1	2024-05-16	Ordering Information
1.2	2025-01-16	Features
1.3	2025-07-11	Ordering Information Characteristics



EU RoHS and China RoHS compliant product

此产品符合欧盟 RoHS 指令的要求；
按照中国的相关法规和标准，
不含有毒有害物质或元素。

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